

MATSUSHIMA

Serial No.: 10/052,345

Response to office action dated February 27, 2004

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-8 (Canceled).

Claim 9 (Original): A semiconductor device comprising:

a plurality of scanning lines;

a plurality of signal lines arranged to cross said scanning lines;

a switching element provided at an intersection of one of said scanning lines and one of said signal lines;

an inter-layer insulating film made of an organic material formed above said scanning lines, said signal lines and said switching element;

a picture element electrode formed above said inter-layer insulating film; and

an additional capacity common wiring for holding a video signal, an additional capacity section being formed between said picture element electrode and said additional capacity common wiring, said additional capacity common wiring being formed above said inter-layer insulating film.

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Claim 10 (Original): The semiconductor device according to claim 9, wherein said additional capacity common wiring is provided at least in a position where said additional capacity common wiring overlaps said switching element.

Claim 11 (Original): The semiconductor device according to claim 10, wherein said additional capacity common wiring covers at least a PN junction in the switching element and functions as a light shielding film.

Claim 12 (Original): The semiconductor device according to claim 9, wherein said additional capacity common wiring is provided in a position where said additional capacity common wiring overlaps at least said scanning lines or said signal lines.

Claim 13 (Original): The semiconductor device according to claim 9, wherein said additional capacity common wiring is made of the same material as a metal for obtaining ohmic contact of a drain electrode of said switching element with the picture element electrode.

Claim 14 (Original): The semiconductor device according to claim 9, wherein said scanning lines and said signal lines are formed on one of paired substrates and a counter substrate which is the other one of paired substrates does not have a black matrix.

Claim 15 (Original): The semiconductor device according to claim 9, wherein the dielectric constant of an insulating film used as a dielectric of the additional capacity

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section is larger than the dielectric constant of the organic material of said inter-layer insulating film.

Claim 16 (Original): The semiconductor device according to claim 15, wherein the dielectric of the additional capacity is made of an anodic oxide film.

Claims 17-22 (Canceled).

Claim 23 (Currently Amended): A semiconductor device comprising:
a scanning line;
a signal line crossing the scanning line;
a switching element provided at an intersection of the scanning line and the signal lines;
an inter-layer insulating film comprising an organic material formed above the scanning line, the signal line and the switching element;
a picture element electrode formed above the inter-layer insulating film; and
an additional capacity electrode formed above the inter-layer insulating film,
wherein ~~an additional capacity section comprises~~ the picture element electrode and the additional capacity electrode comprise part of an additional capacity section.

Claim 24 (Previously Presented): The semiconductor device according to claim 23, wherein the additional capacity electrode overlaps the switching element.

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Claim 25 (Previously Presented): The semiconductor device according to claim 23, wherein the additional capacity electrode shields light from a PN junction of the switching element.

Claim 26 (Previously Presented): The semiconductor device according to claim 23, wherein the additional capacity electrode overlaps at least one of the scanning line and the signal line.

Claim 27 (Previously Presented): The semiconductor device according to claim 23, further comprising:

an ohmic contact between an electrode of the switching device and the picture element electrode,

wherein the additional capacity electrode is made of the same material as the ohmic contact.

Claim 28 (Previously Presented): The semiconductor device according to claim 23, wherein the scanning line and the signal line are formed on one of a pair of substrates of the semiconductor device and no black matrix is formed on the other one of the pair of substrates.

Claim 29 (Previously Presented): The semiconductor device according to claim 23, wherein the additional capacity section further comprises an insulating film

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having a dielectric constant greater than a dielectric constant of the organic material of the inter-layer insulating film.

Claim 30 (Previously Presented): The semiconductor device according to claim 29, wherein the insulating film of the additional capacity section comprises an anodic oxide film.